Investigation of Turn-on and Turn-off Characteristics of Enhancement-Mode Gallium Nitride Power Transistors

**Abstract:** In this paper, turn-on and turn-off switching behavior of 650V enhancement-mode (e-mode) Gallium Nitride (GaN) power Field Effect Transistors (FETs) are investigated.

1. Introduction
2. GaN Modeling
3. Switching Behaviour of GaN
4. Effect of Parasitic Elements
5. Results
6. Conclusions